Is Now Part of

ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

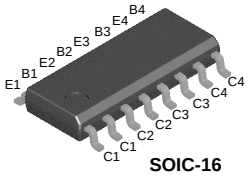
Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FAIRCHILD
SEMICONDUCTOR®

MMPQ2222

NPN Multi-Chip General Purpose Amplifier

- This device is for use as a medium power amplifier and switch requiring collector currents up to 500mA.
- Sourced from process 19.



SOIC-16
Mark: MMPQ2222

Absolute Maximum Ratings * T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	30	V
V_{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	500	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	- 55 ~ +155	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage *	I_C = 10mA, I_B = 0	30		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 10μA, I_E = 0	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_C = 10μA, I_C = 0	5.0		V
I_{CBO}	Collector Cutoff Current	V_{CB} = 50V, I_E = 0		50	nA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 3.0V, I_C = 0		50	nA
On Characteristics *					
h_{FE}	DC Current Gain	I_C = 10mA, V_{CE} = 10V I_C = 150mA, V_{CE} = 1.0V * I_C = 150mA, V_{CE} = 1.0V *	75 100 50		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage *	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA		0.4 1.6	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage *	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA		1.3 2.6	V V
Small Signal Characteristics					
f_T	Current GAin Bandwidth Product	I_C = 20mA, V_{CE} = 20V, f = 100MHz		300	MHz
C_{obo}	Output Capacitance	V_{CB} = 10V, I_E = 0, f = 100kHz		4.0	pF
C_{ibo}	Input Capacitance	V_{EB} = 0.5V, I_E = 0, f = 100kHz		20	pF
NF	Noise Figure	I_C = 100μA, V_{CE} = 10V, R_S = 1.0kΩ, f = 1.0kHz		2.0	dB

* Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%

Thermal Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
P_D	Total Device Dissipation Derate above 25°C	1000 8.0	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Effective 4 Die Each Die	 125 240	 °C/W °C/W

Typical Characteristics

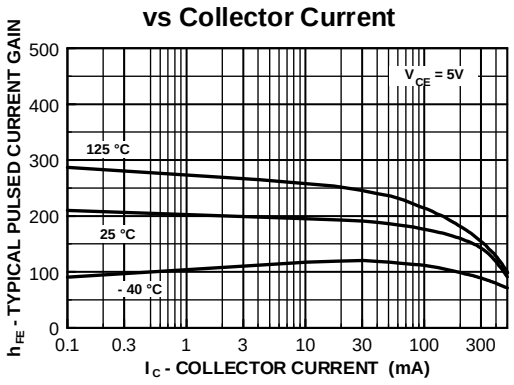


Figure 1. Typical Pulsed Current Gain vs Collector Current

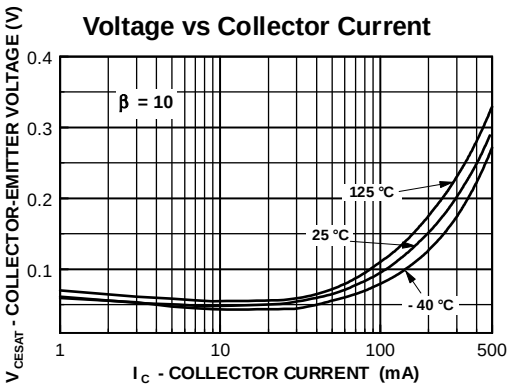


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

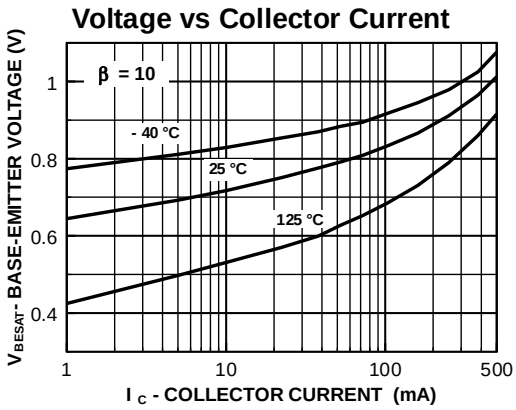


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

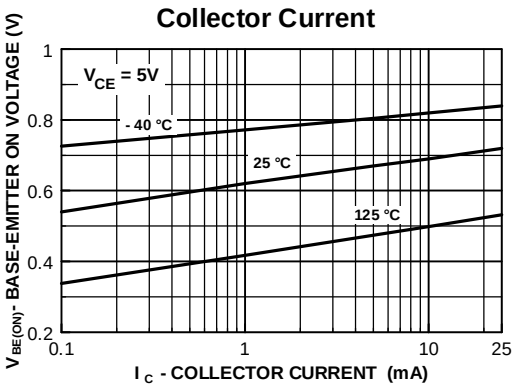


Figure 4. Base-Emitter On Voltage vs Collector Current

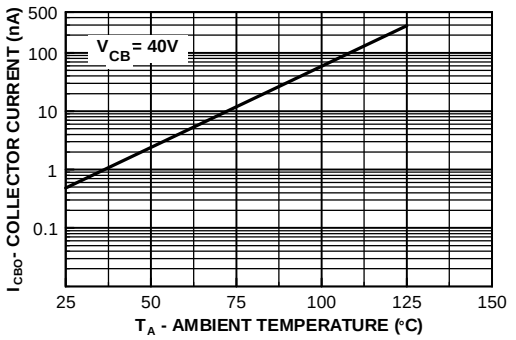


Figure 5. Collector Cutoff Current vs Ambient Temperature

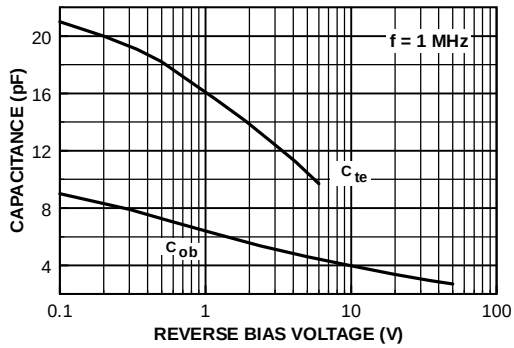


Figure 6. Emitter Transition and Output Capacitance vs Reverse Bias Voltage

Typical Characteristics (Continued)

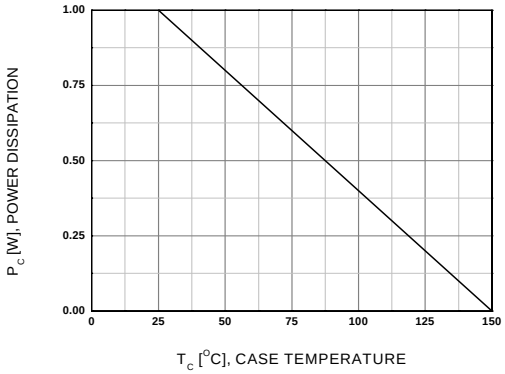


Figure 7. Power Dissipation vs Ambient Temperature

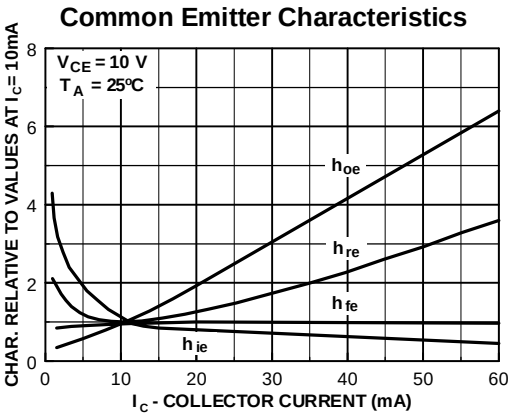


Figure 8. Common Emitter Characteristics

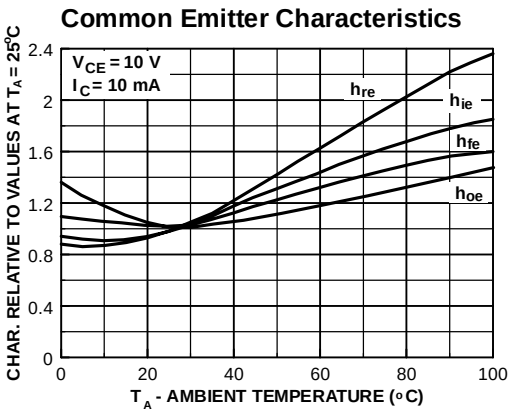


Figure 9. Common Emitter Characteristics

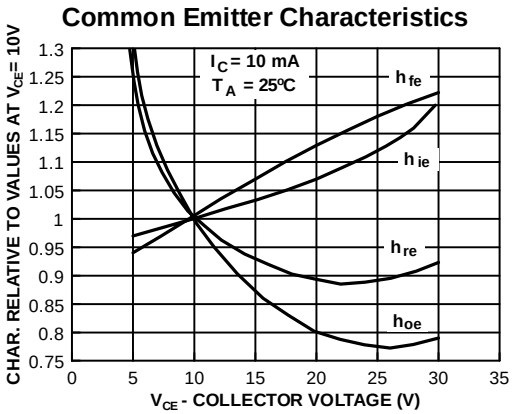


Figure 10. Common Emitter Characteristics

Test Circuit

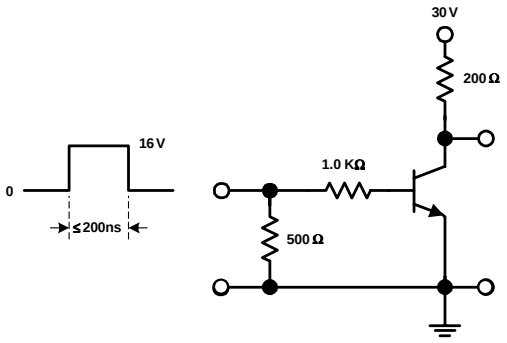


Figure 1. Saturated Turn-On Switching Time

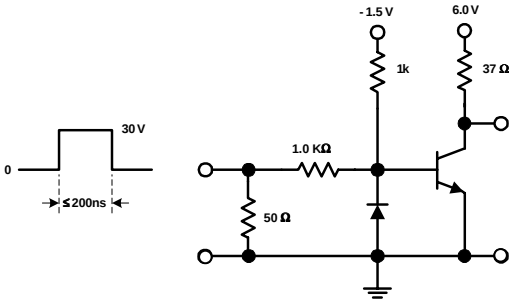
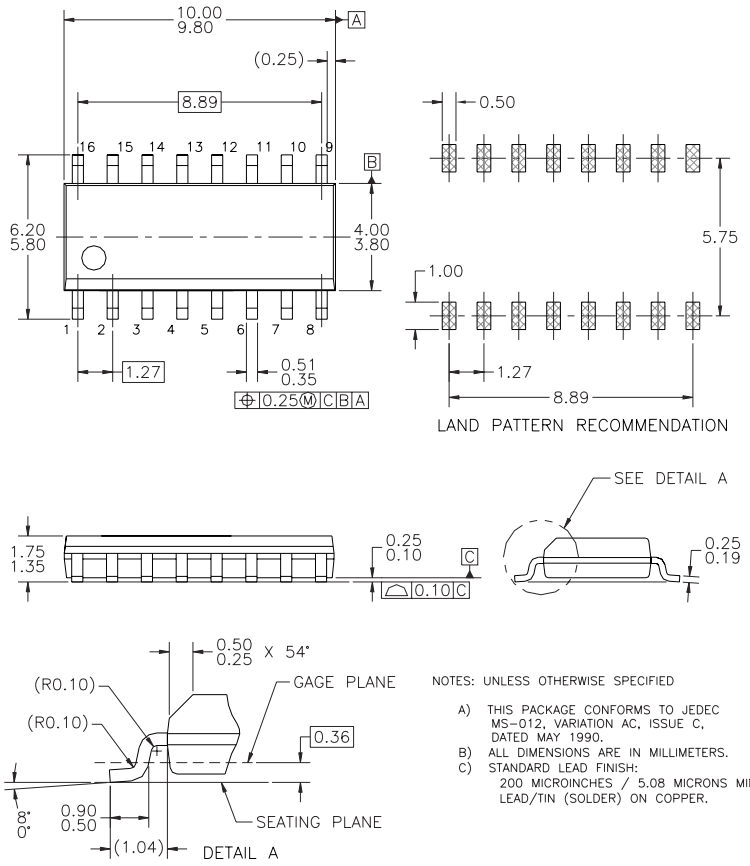


Figure 2. Saturated Turn-Off Switching Time

Package Dimensions

SOIC-16



NOTES: UNLESS OTHERWISE SPECIFIED

A) THIS PACKAGE CONFORMS TO JEDEC MS-012, VARIATION AC, ISSUE C, DATED MAY 1990.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) STANDARD LEAD FINISH: 200 MICROINCHES / 5.08 MICRONS MIN. LEAD/TIN (SOLDER) ON COPPER.

Dimensions in Millimeters

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FAST®	ISOPLANAR™	Power247™	Stealth™
ActiveArray™	FASTr™	LittleFET™	PowerEdge™	SuperFET™
Bottomless™	FPS™	MICROCOUPLER™	PowerSaver™	SuperSOT™-3
CoolFET™	FRFET™	MicroFET™	PowerTrench®	SuperSOT™-6
CROSSVOLT™	GlobalOptoisolator™	MicroPak™	QFET®	SuperSOT™-8
DOME™	GTO™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	HiSeC™	MSX™	QT Optoelectronics™	TinyLogic®
E^2CMOS™	I^2C™	MSXPro™	Quiet Series™	TINYOPTO™
EnSigna™	*i-Lo*™	OCX™	RapidConfigure™	TruTranslation™
FACT™	ImpliedDisconnect™	OCXPro™	RapidConnect™	UHC™
FACT Quiet Series™		OPTOLOGIC®	µSerDes™	UltraFET®
Across the board. Around the world.™		OPTOPLANAR™	SILENT SWITCHER®	VCX™
The Power Franchise®		PACMAN™	SMART START™	
Programmable Active Droop™		POP™	SPM™	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative